

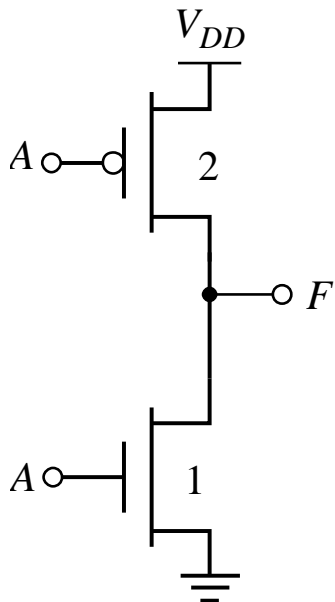
EE 466/586
VLSI Design

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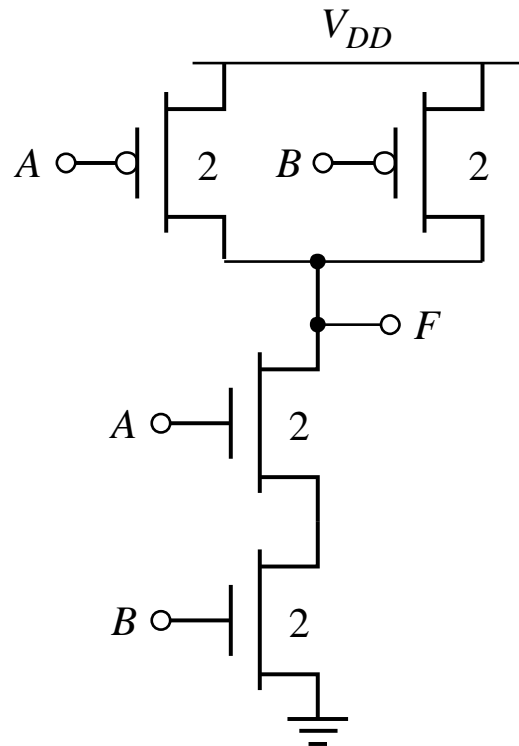
Lecture 7
Static MOS Gate Circuits

CMOS Gate Sizing

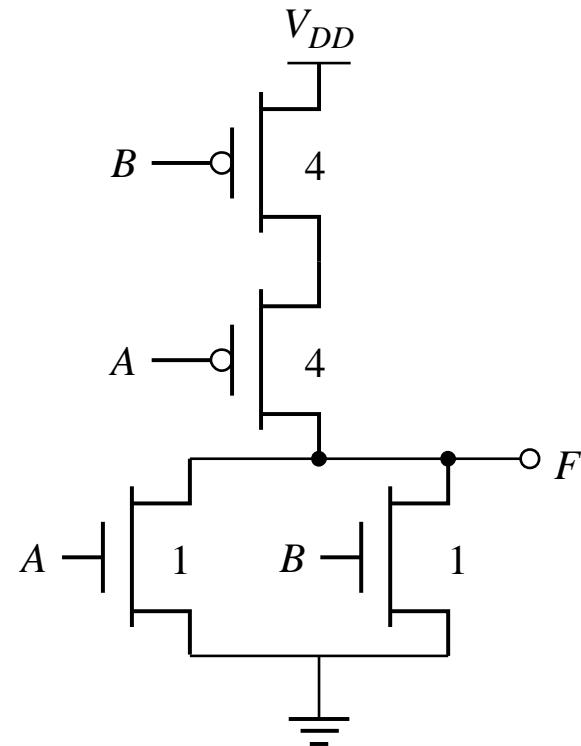
- NAND and NOR gate sizing
- Follow board notes



Inverter

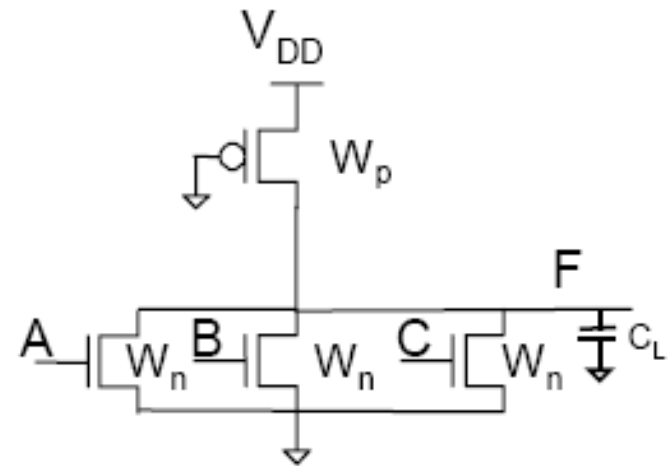
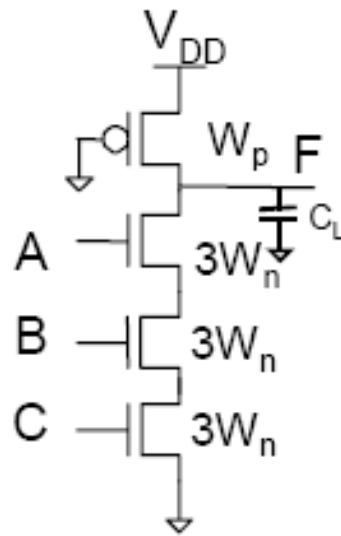
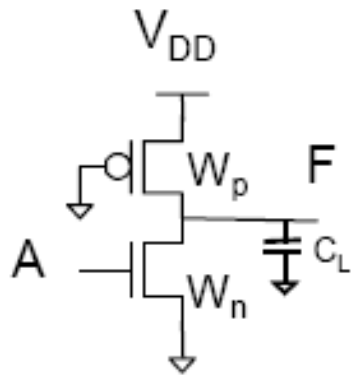


2-input NAND



2-input NOR

Pseudo-NMOS Gate Sizing

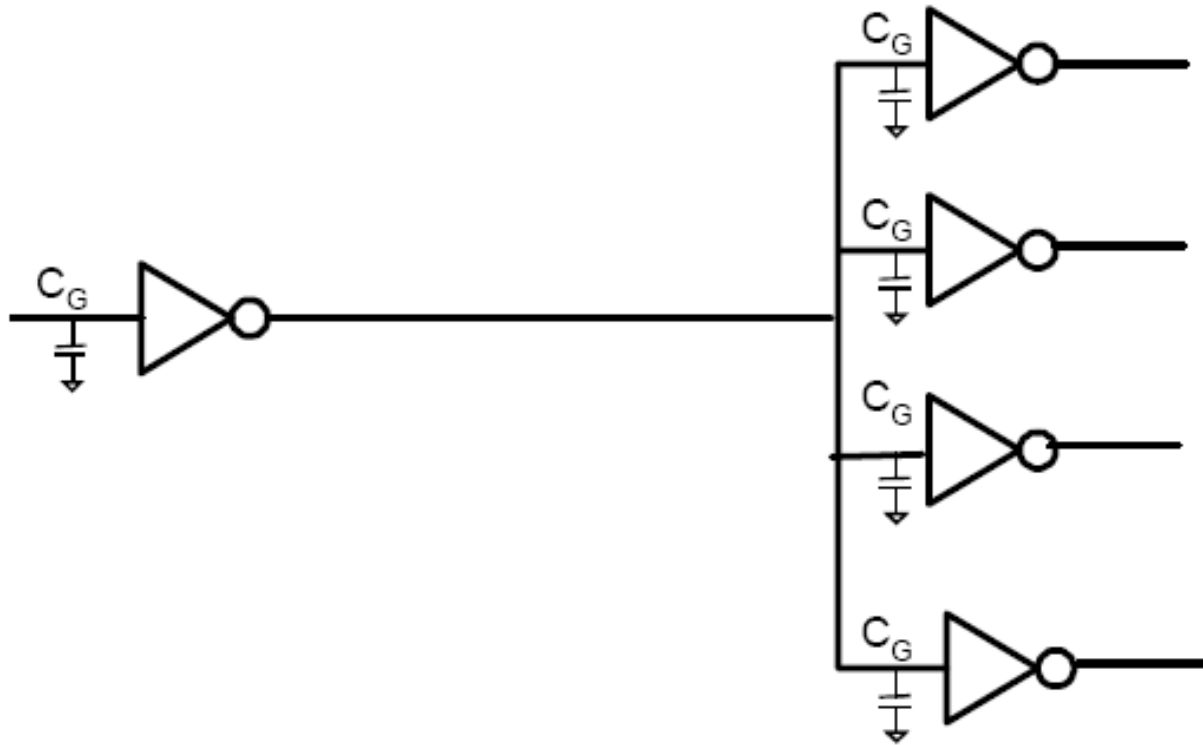


Fanin and Fanout Considerations

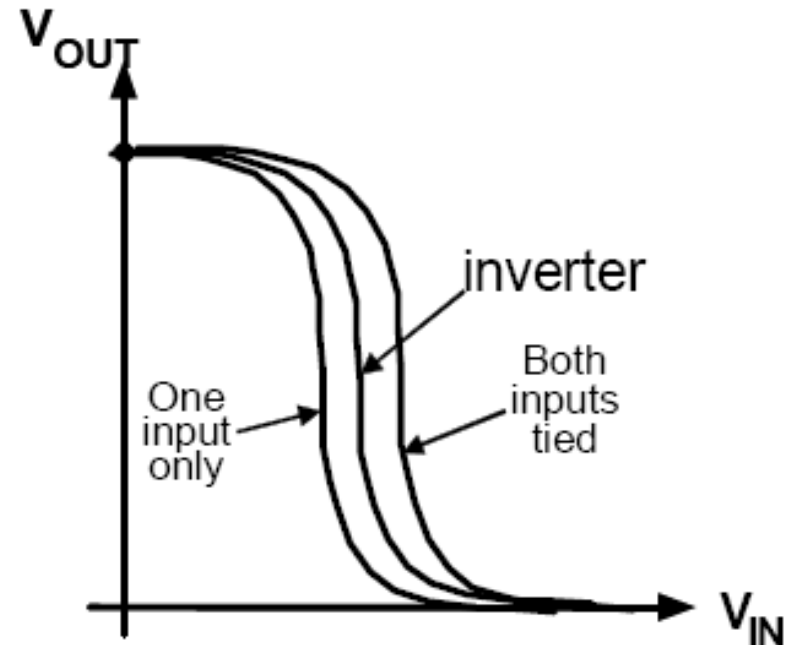
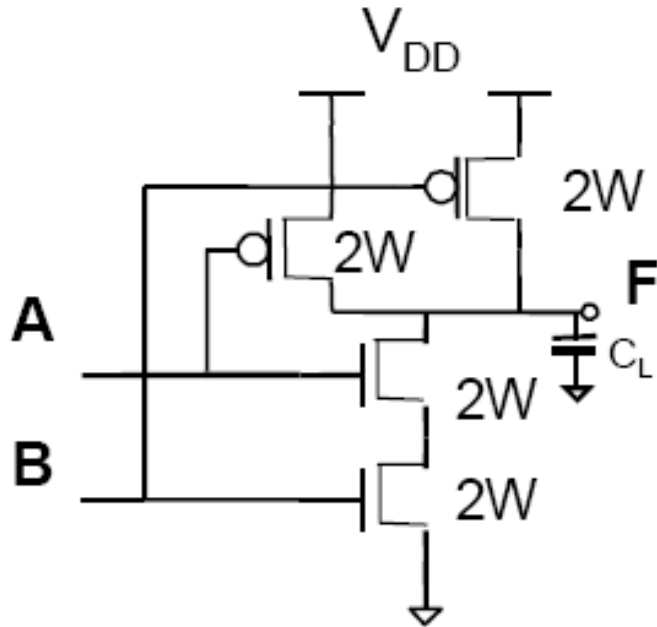
- Gates with a large number of inputs (high fan-in gates)
 - Too high resistance
 - Area penalty
- Follow board notes
- Fan Out
 - Output driving capability

Fan Out

10

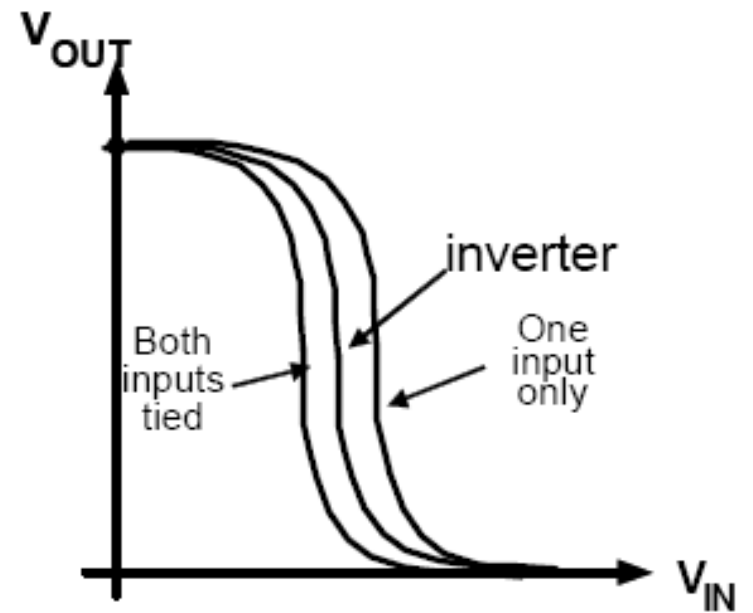
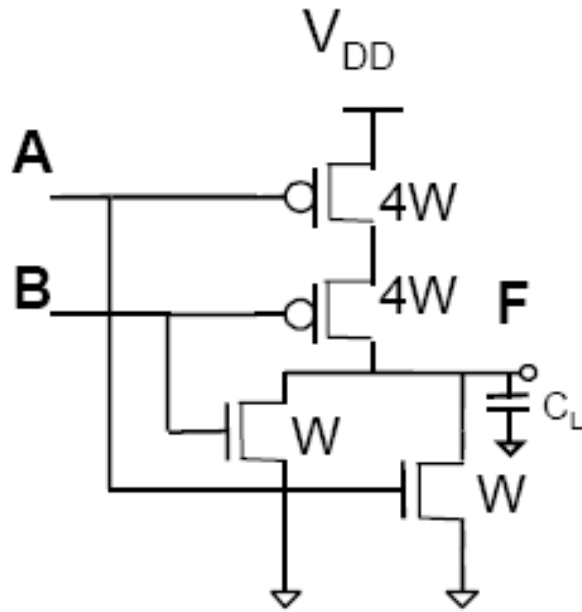


VTC of NAND Gates



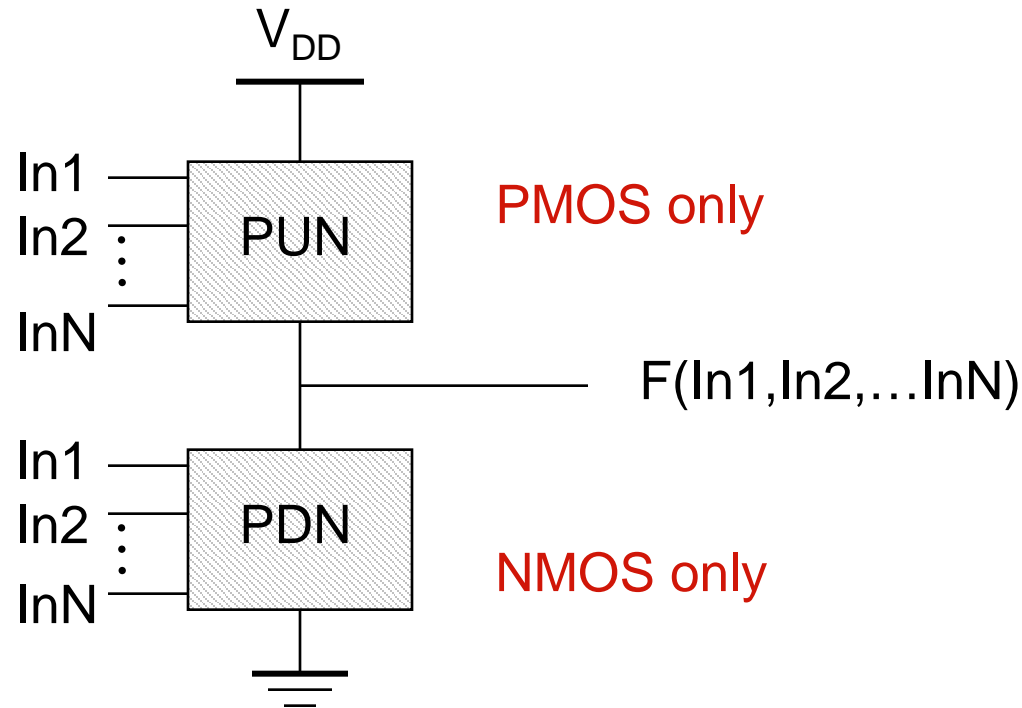
□ If input A is held high while input B switched from low to high, the gate is equivalent to an inverter with a $2W$ pull-up device and a $2W$ pull-down device. The resulting transfer characteristic would shift to the left of the standard inverter.

VTC of NOR Gates



Static Complementary CMOS

- The function of the PUN is to provide a connection between the output and V_{DD} anytime the output of the logic gate is meant to be 1
- Similarly the role of the PDN is to connect the output to GND when the output is meant to be 0

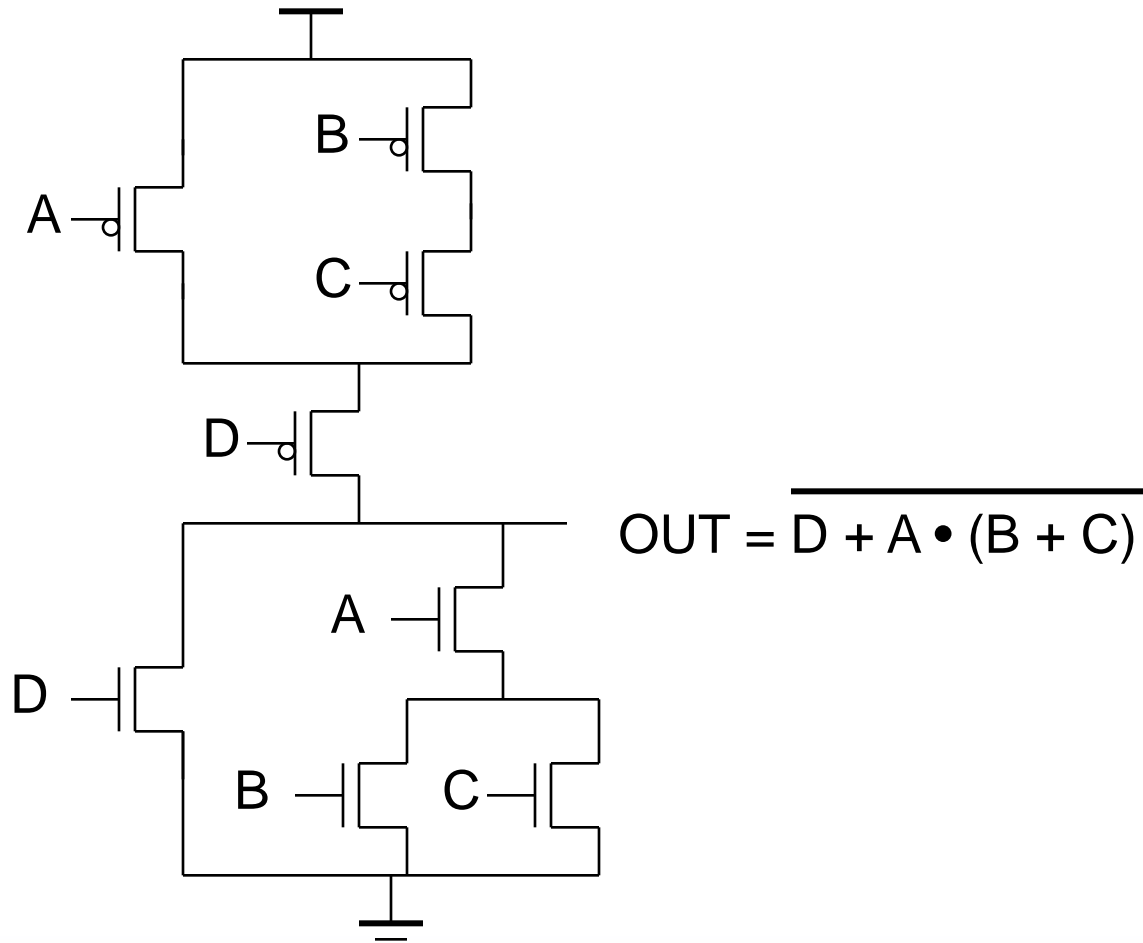


PUN and PDN are **dual** logic networks

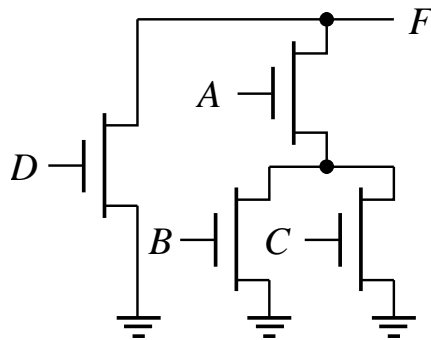
NMOS as PDN & PMOS as PUN

- ❑ NMOS device can pull the output all the way down to GND, but the PMOS device can pull it down to V_{tp}
- ❑ NMOS transmits a strong 0
- ❑ PMOS transmits a strong 1

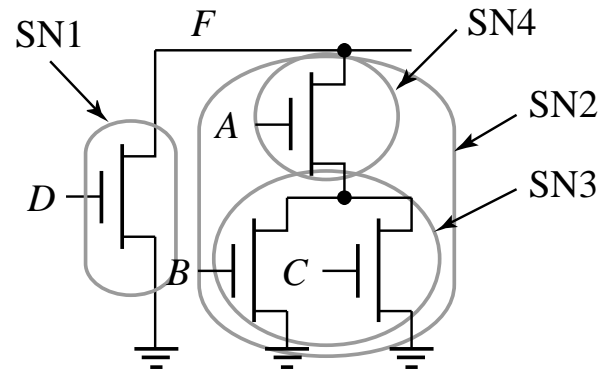
Complex CMOS Gate



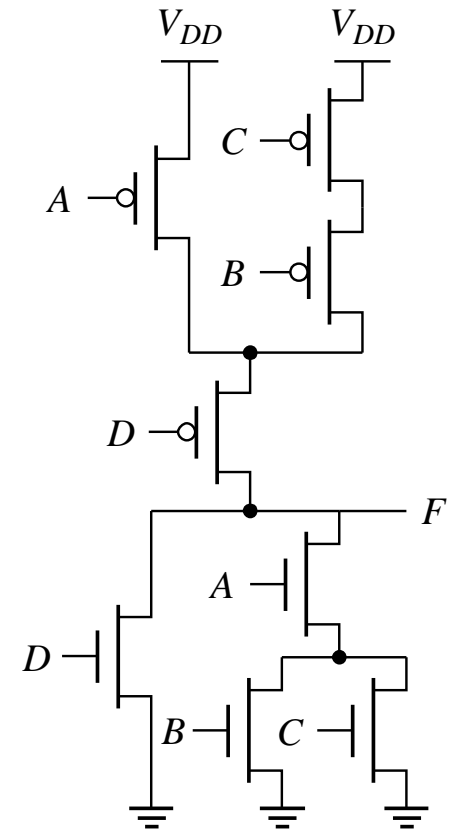
Constructing a Complex Gate



(a) pull-down network

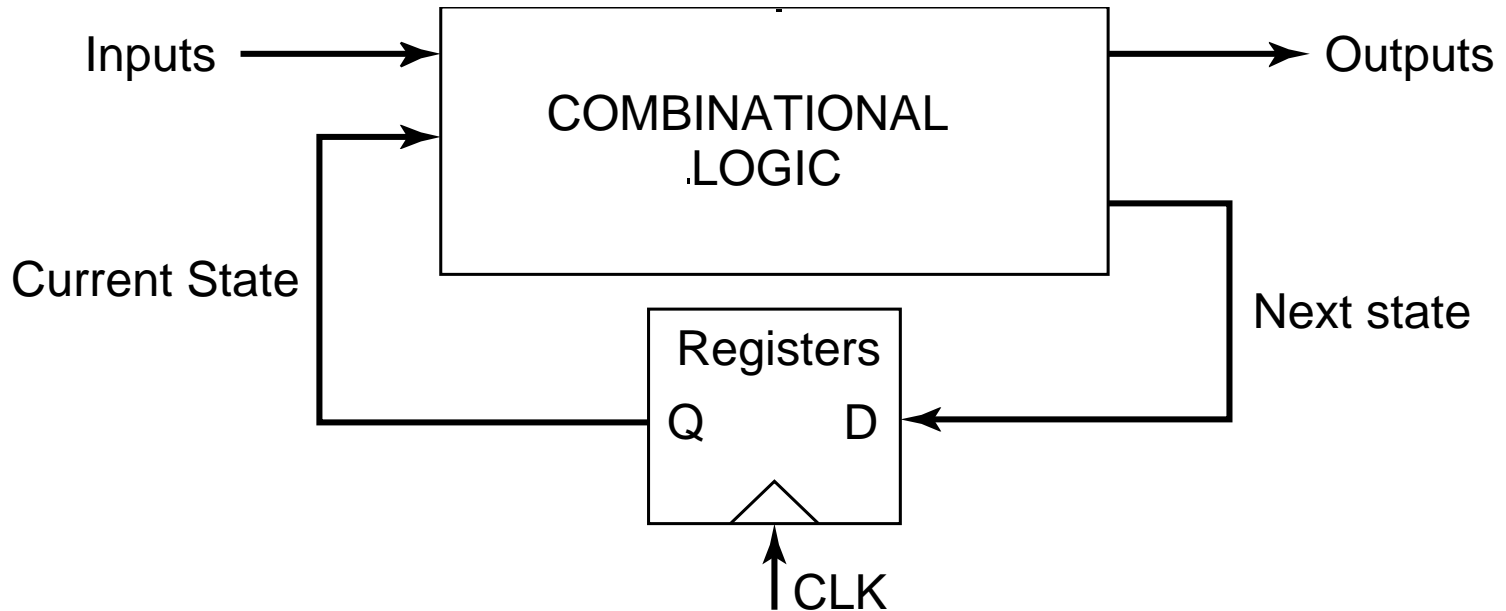


(b) Deriving the pull-up network hierarchically by identifying sub-nets



(c) complete gate

Sequential Logic



2 storage mechanisms

- positive feedback
- charge-based

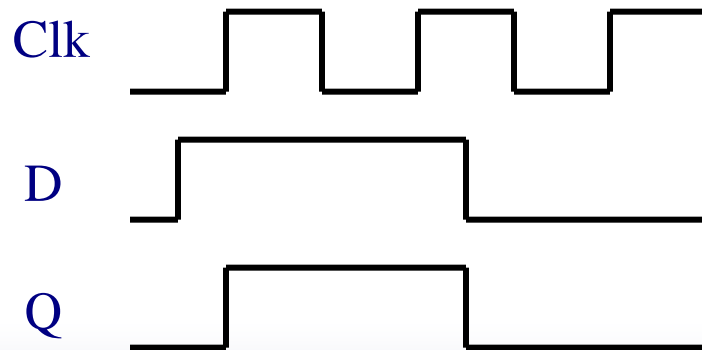
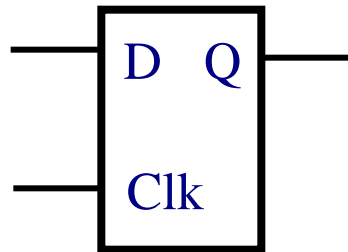
A latch is **level sensitive**

A register is **edge-triggered**

Latch versus Register

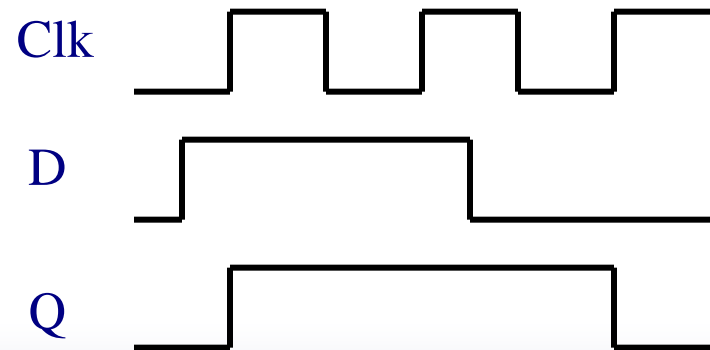
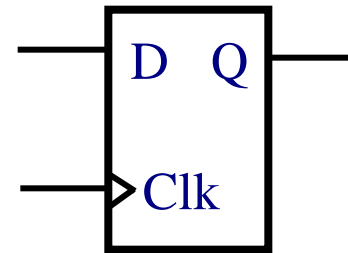
□ Latch

Stores data depending on the level of the clock



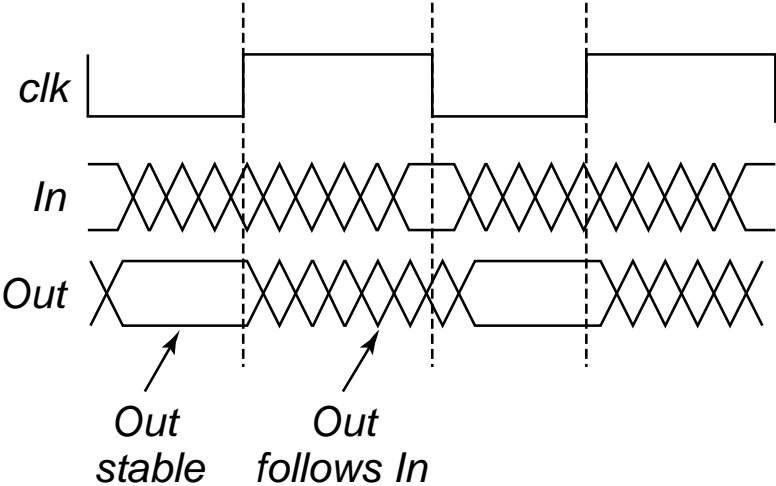
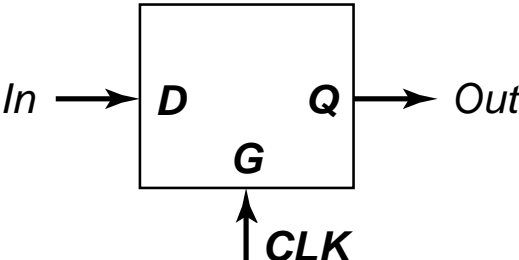
□ Register

stores data when clock rises

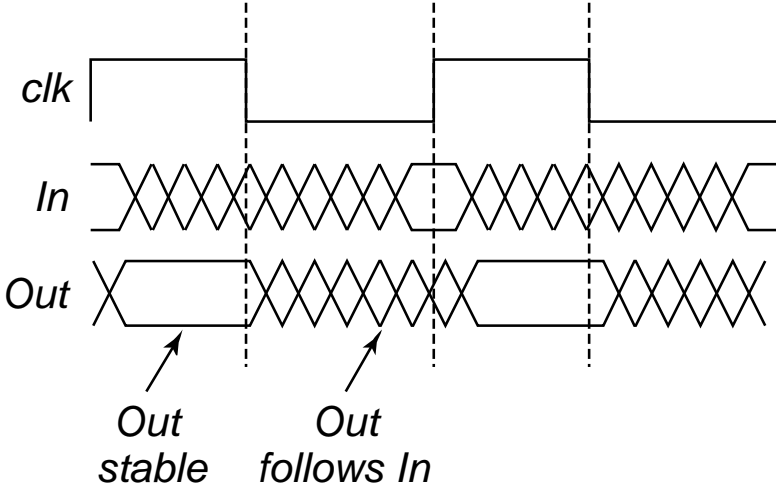
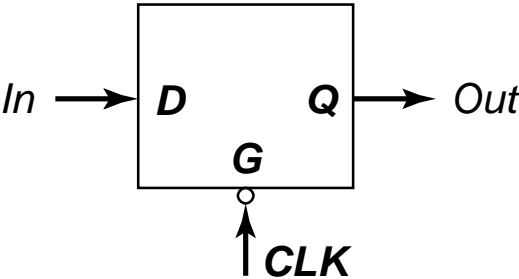


Latches

Positive Latch



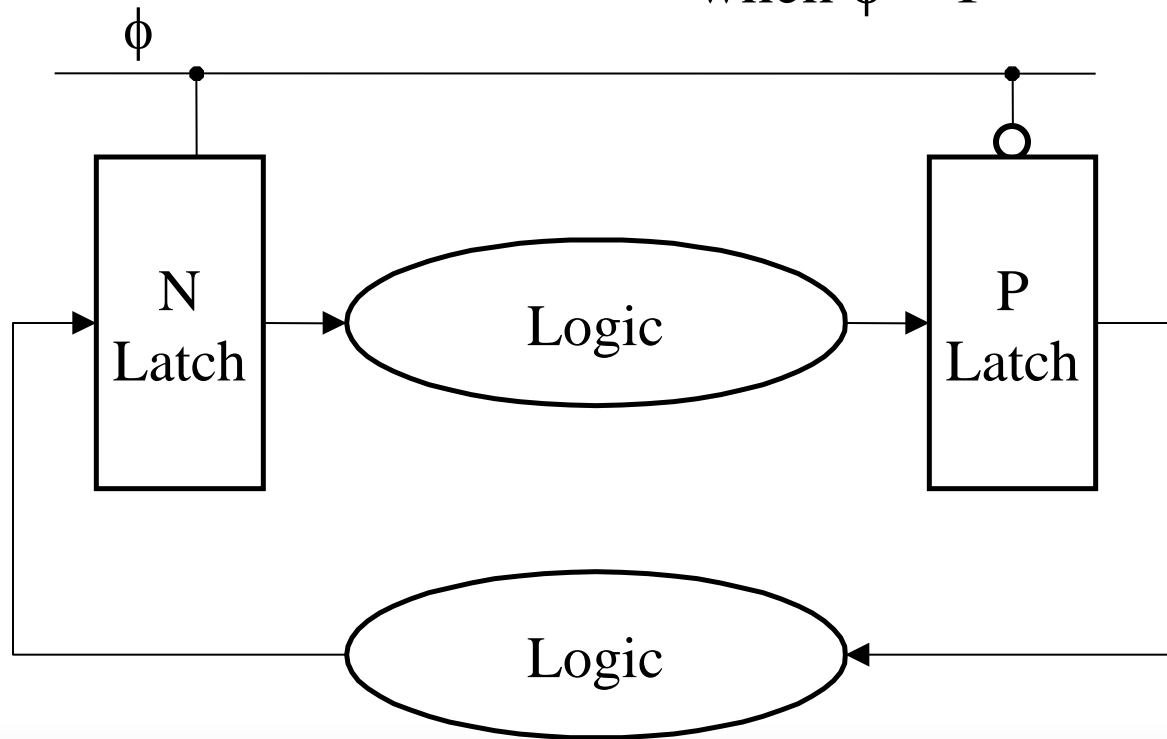
Negative Latch



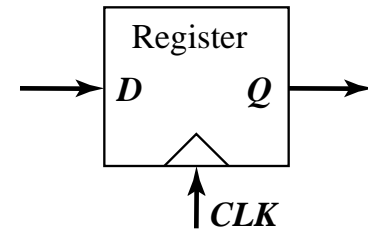
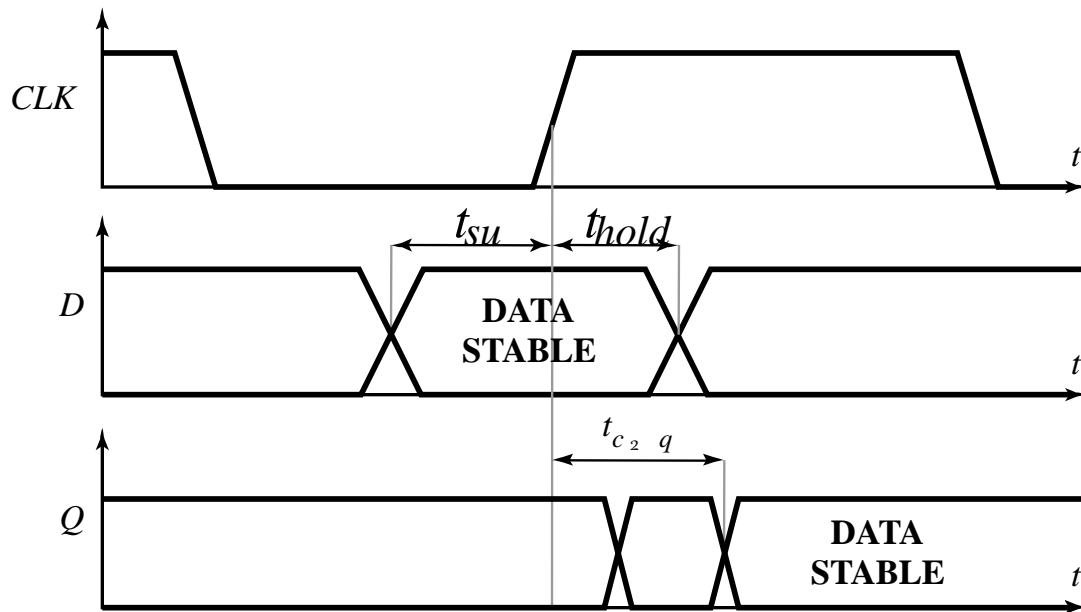
Latch-Based Design

- N latch is transparent when $\phi = 0$

- P latch is transparent when $\phi = 1$



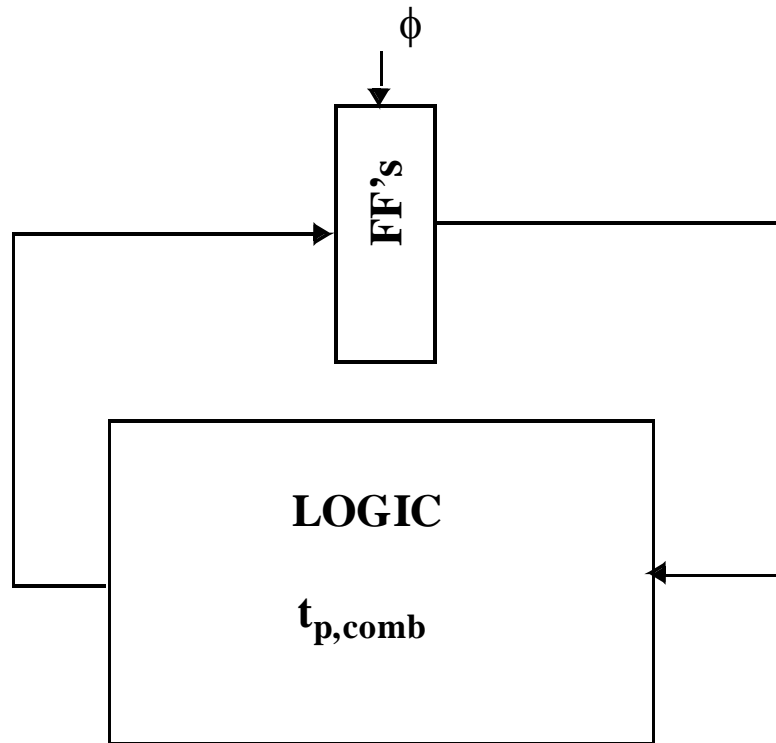
Timing Definitions



Timing Definitions

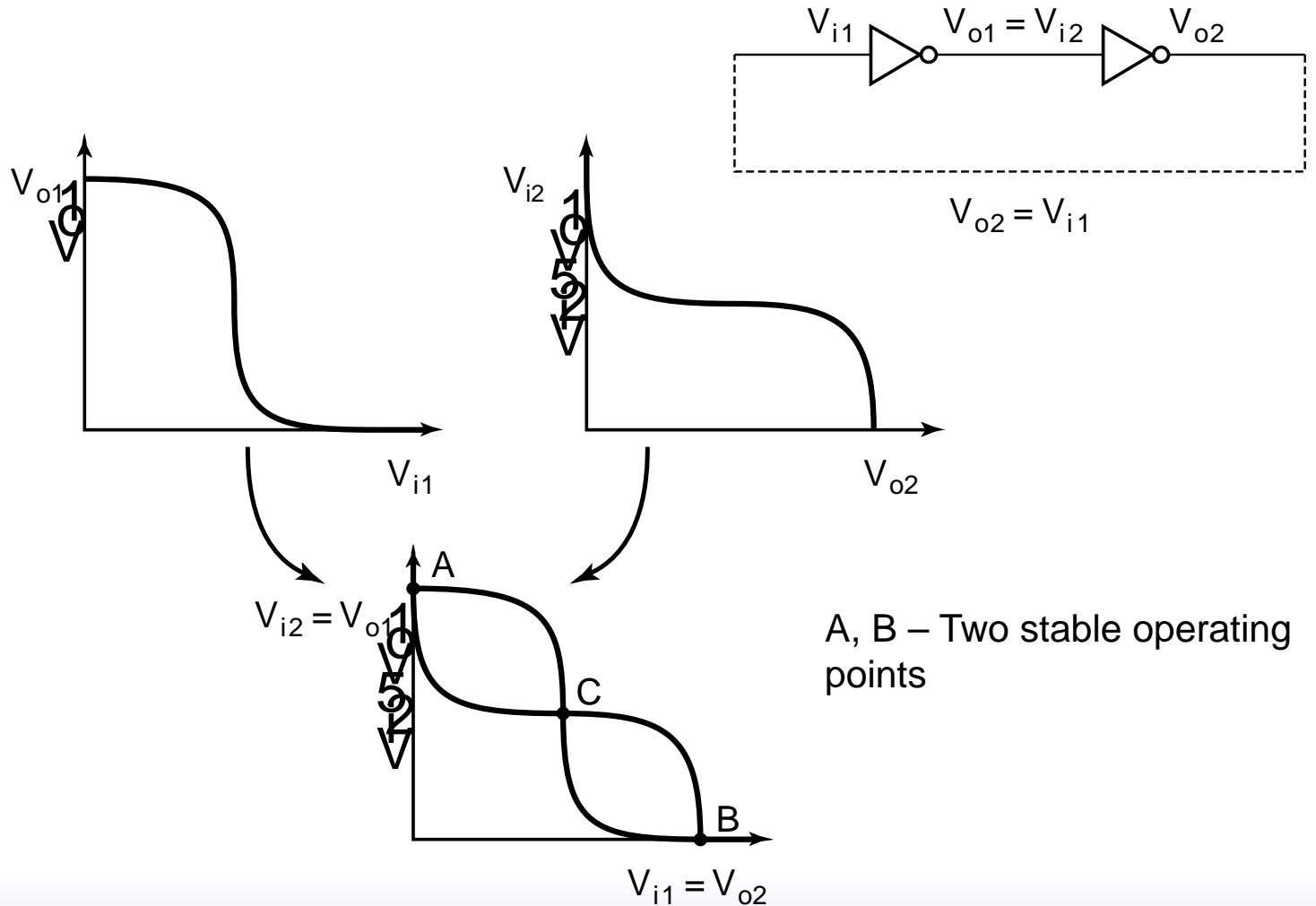
- ❑ T_{su} (Setup time)
 - Incoming data must be stable before the clock arrives
- ❑ T_{hold} (Hold time)
 - The length of time the data remains stable after the clock arrives for proper operation
- ❑ If the data is stable before the setup time and continues to be stable after the hold time, the register will properly capture the data
- ❑ T_{clk-Q} (clk to Q delay)
 - This is the delay from the time the clock arrives to the point at which the Q output stabilizes

Maximum Clock Frequency

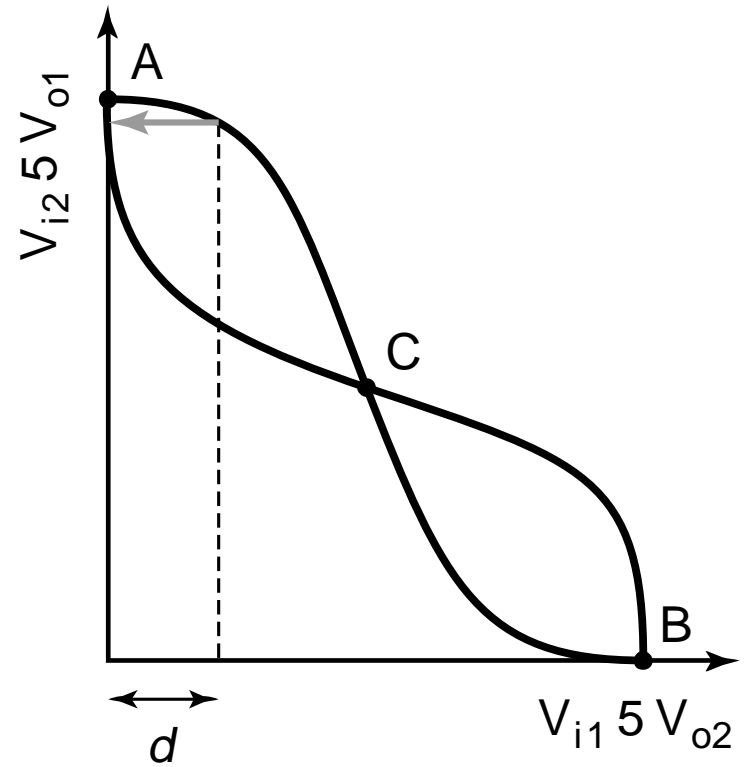
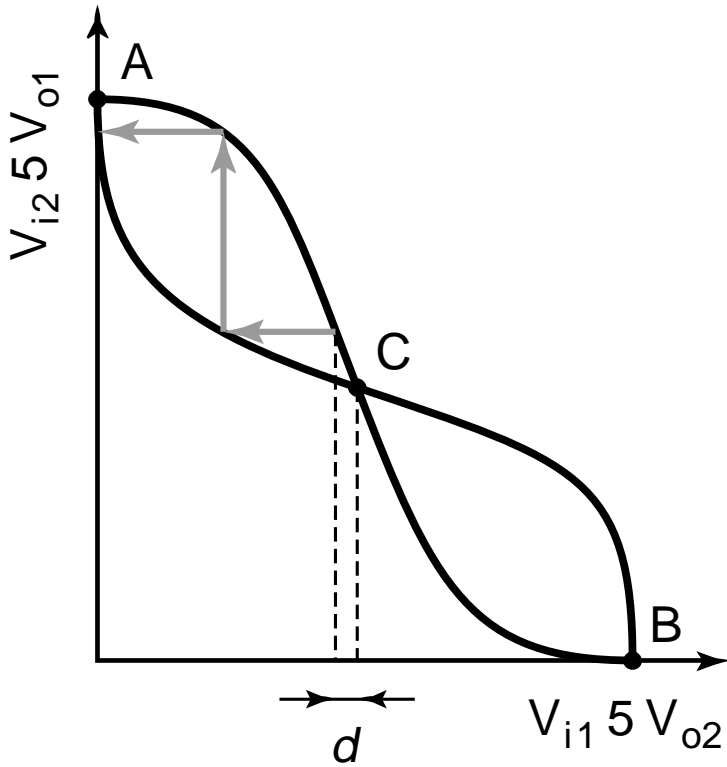


$$t_{clk-Q} + t_{p,comb} + t_{setup} = T$$

Positive Feedback: Bi-Stability



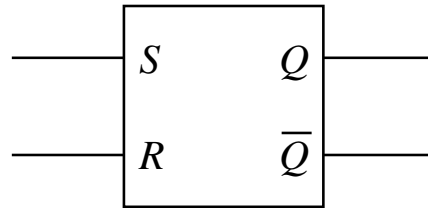
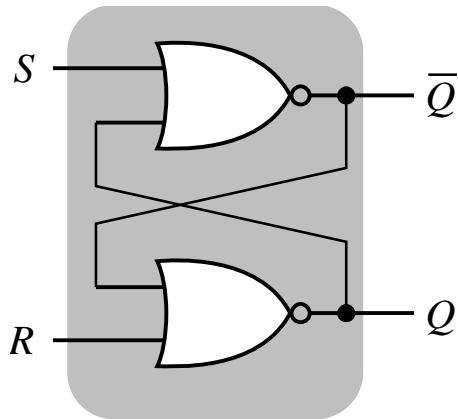
Meta-Stability



Gain should be larger than 1 in the transition region

Cross-Coupled Pairs

NOR-based set-reset

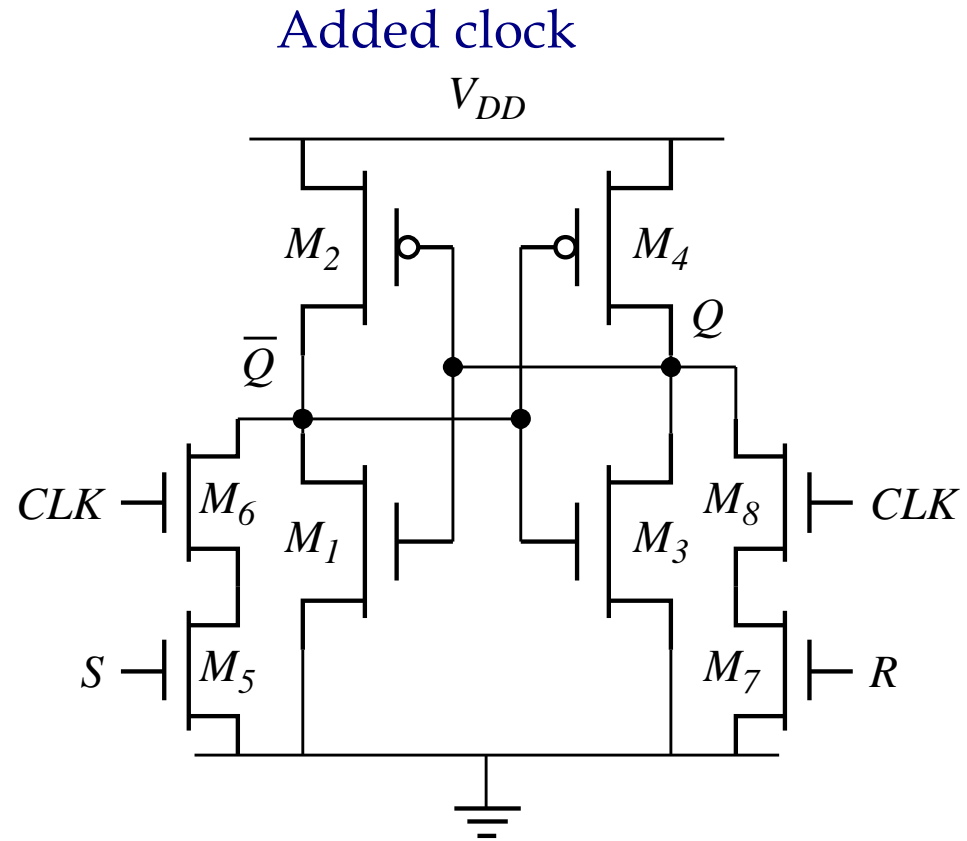
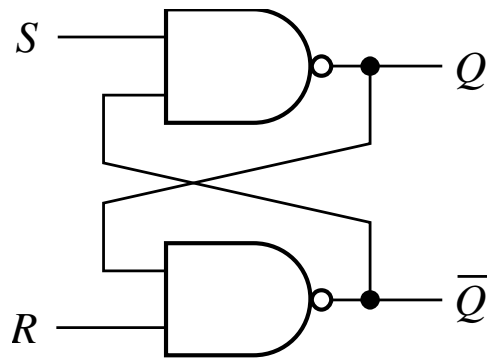


S	R	Q	\bar{Q}
0	0	Q	\bar{Q}
1	0	1	0
0	1	0	1
1	1	0	0

Forbidden State

Cross-Coupled NAND

Cross-coupled NANDs



This is not used in datapaths any more,
but is a basic building memory cell